

isc Silicon PNP Power Transistor

2SB1392

DESCRIPTION

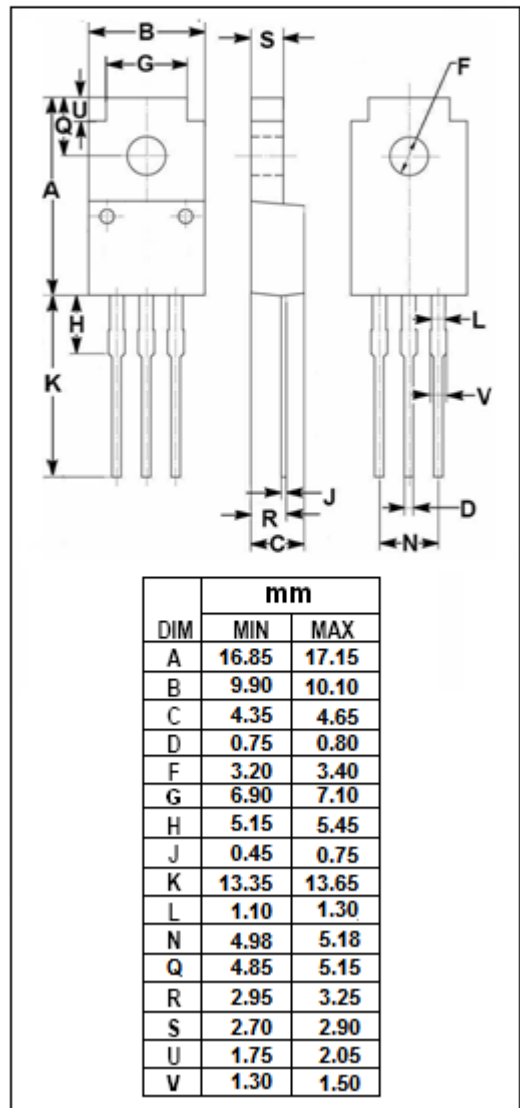
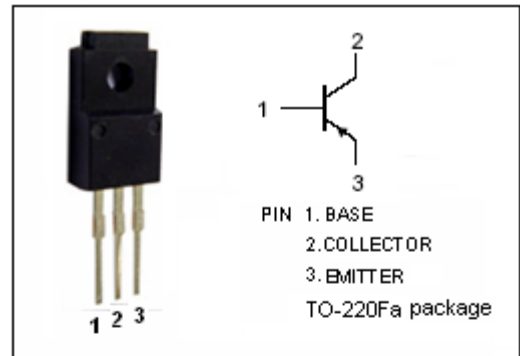
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -60V(\text{Min.})$
- Good Linearity of h_{FE}

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-8	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	25	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}; R_{BE} = \infty$	-60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\ \mu\text{A}; I_E = 0$	-70			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\ \mu\text{A}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-1.2	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -1\text{A}; V_{CE} = -4\text{V}$			-1.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -50\text{V}; I_E = 0$			-10	μA
I_{CEO}	Collector Cutoff Current	$V_{CE} = -50\text{V}; R_{BE} = \infty$			-10	μA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	60		200	
h_{FE-2}	DC Current Gain	$I_C = -0.1\text{A}; V_{CE} = -4\text{V}$	35			

◆ h_{FE-1} Classifications

B	C
60-120	100-200